

IRF7492TRPBF-VB Datasheet N-Channel 200-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)		
200	0.065 at V _{GS} = 10 V	5.2		
	0.072 at V _{GS} = 6.0 V	4.1		

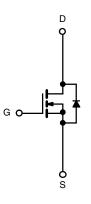
FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- Trench Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC



HALOGEN FREE Available

SO-8 S D 8 1 S D 2 7 S D 6 3 G D 4 5 Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25 \degree C$, unless otherwise noted					
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	200		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current /T 150 °C)a	T _A = 25 °C	L	5.2	3.35	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C	- I _D	4.6	2.7	
Pulsed Drain Current		I _{DM}	40		А
Avalanch Current	L = 0.1 mH	I _{AS}	15		
Continuous Source Current (Diode Conduction) ^a	I _S	2.6	1.3		
	T _A = 25 °C	P _D	3.1 1.56		W
Maximum Power Dissipation ^a	T _A = 70 °C		2.0	1.0	vv
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55	to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manimum has bien to Anabien 18	t ≤ 10 s	R _{thJA}	33	40	
Maximum Junction-to-Ambient ^a	Steady State	¹ 'thJA	65	80	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	17	21	

Notes:

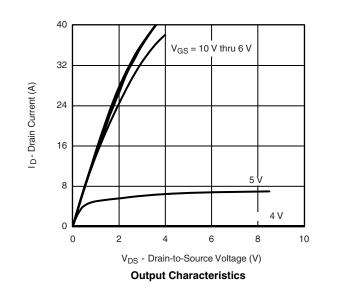
a. Surface Mounted on 1" x 1" FR4 board.

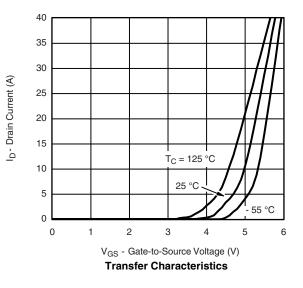
SPECIFICATIONS $T_J = 25 \text{ °C}$, unless otherwise noted								
Parameter	Symbol	ymbol Test Conditions		Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$ 2				V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 20 V$			± 100	nA		
Zara Cata Valtaga Drain Current	1	$V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}$			1			
Zero Gate Voltage Drain Current	IDSS	V_{DS} = 160 V, V_{GS} = 0 V, T_{J} = 55 °C			5	μΑ		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5$ V, V_{GS} = 10 V	40			А		
_	Б	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 4.0 \text{ A}$		0.065		0		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 6.0 \text{ V}, \text{ I}_{D} = 4.0 \text{ A}$		0.072		Ω		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 5 \text{ A}$		19		S		
Diode Forward Voltage ^a	V _{SD}	$I_{\rm S} = 2.8$ A, $V_{\rm GS} = 0$ V		0.75	1.2	V		
Dynamic ^b								
Total Gate Charge	Qg			34	42			
Gate-Source Charge	Q _{gs}	$V_{DS} = 100 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 4.0 \text{ A}$		7.5		nC		
Gate-Drain Charge	Q _{gd}			12.0		1		
Gate Resistance	Rg		0.2	0.85	1.3	Ω		
Turn-On Delay Time	t _{d(on)}			14	20			
Rise Time	t _r	V_{DD} = 100 V, R_L = 25 Ω		20	30			
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ 4.0 A, V_GEN = 10 V, R_g = 6 Ω		32	50	ns		
Fall Time	t _f			25	35			
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 2.8 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		70	100			

Notes: a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

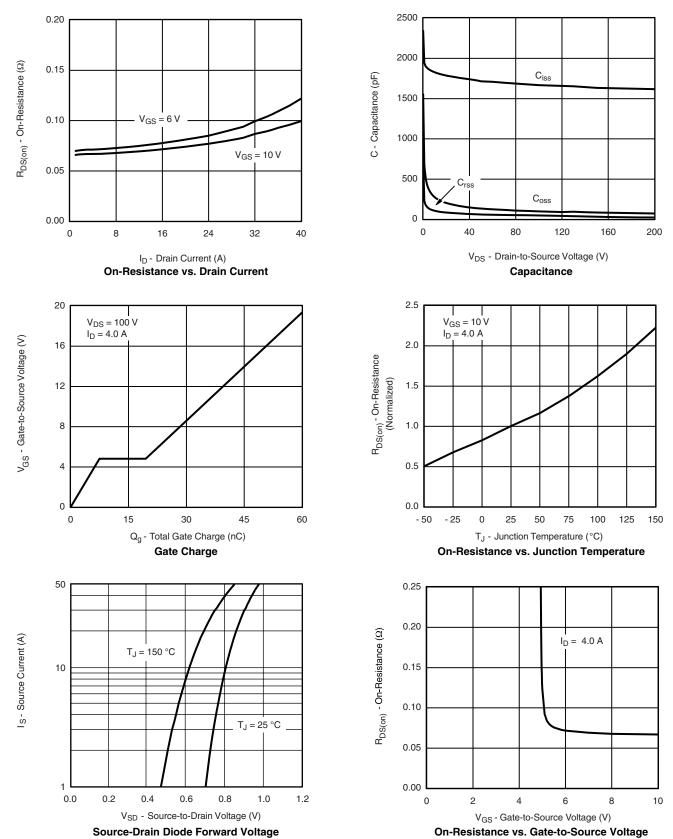




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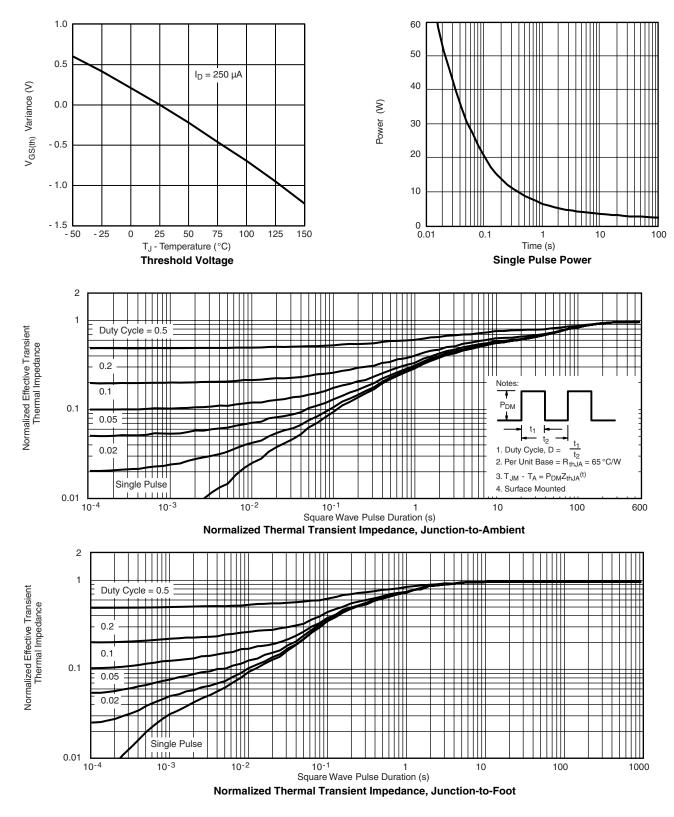


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



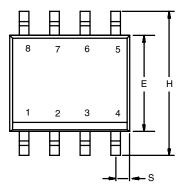


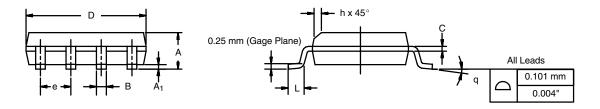
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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012



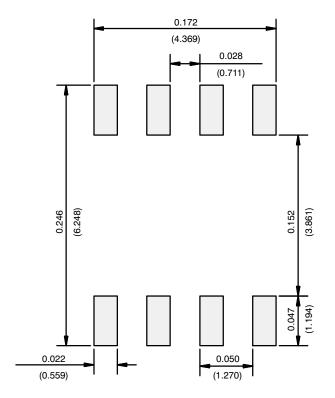


	MILLIM	IETERS	INCHES			
DIM	Min	Мах	Min	Max		
A	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498						

IRF7492TRPBF-VB



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)



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